

# SILICON TRANSISTOR

# FA1L3Z

# MEDIUM SPEED SWITCHING RESISTOR BUILT-IN TYPE NPN TRANSISTOR MINI MOLD

### **PACKAGE DIMENSIONS**

in millimeters

2.8±0.2

1.5

0.65+0.1

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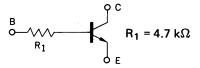
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#### **FEATURES**

• Resistor Built-in TYPE



Complementary to FN1L3Z

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Voltages and Currents (T <sub>a</sub> = 25	°C)		
Collector to Base Voltage	$V_{\sf CBO}$	60	V
Collector to Emitter Voltage	V <sub>CEO</sub>	50	٧
Emitter to Base Voltage	V <sub>EBO</sub>	5	٧
Collector Current (DC)	Ic	100	mΑ
Collector Current (Pulse)	Ic	200	mΑ
Maximum Power Dissipation			
Total Power Dissipation			
at 25 °C Ambient Temperature	$P_T$	200	mW
Maximum Temperatures			
Junction Temperature	T <sub>i</sub>	150	°C
Storage Temperature Range	T <sub>sta</sub>	-55 to +150	°C
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## ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	СВО			100	nA	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0
DC Current Gain	hFE1*	135	450	600		V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 5.0 mA
DC Current Gain	hFE2*	100	380			V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 50 mA
Collector Saturation Voltage	V <sub>CE(sat)</sub> *		0.04	0.2	٧	I <sub>C</sub> = 5.0 mA, I <sub>B</sub> = 0.25 mA
Low-Level Input Voltage	VIL*		0.54	0.5	٧	V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 μA
High-Level Input Voltage	V <sub>IH</sub> *	1.2	0.71		٧	V <sub>CE</sub> = 0.2 V, I <sub>C</sub> = 5.0 mA
Input Resistor	R <sub>1</sub>	3.29	4.7	6.11	kΩ	
Turn-on Time	ton		0.03	0.2	μs	V <sub>CC</sub> = 5 V, V <sub>in</sub> = 5 V
Storage Time	t <sub>stg</sub>		3.2	5.0	μs	RL=1kΩ
Turn-off Time	<sup>t</sup> off		3.4	6.0	μs	PW = 2 μs, Duty Cycle ≦ 2 %

<sup>\*</sup> Pulsed: PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

# h<sub>FE</sub> Classification

Emitter
 Base
 Collector

Marking	L36	L37	L38
hFE1	135 to 270	200 to 400	300 to 600

## TYPICAL CHARACTERISTICS (Ta = 25 °C)

